

**TIL189-1 THRU TIL189-4
TIL190-1 THRU TIL190-4
OPTOCOUPLED/OPTOISOLATORS**

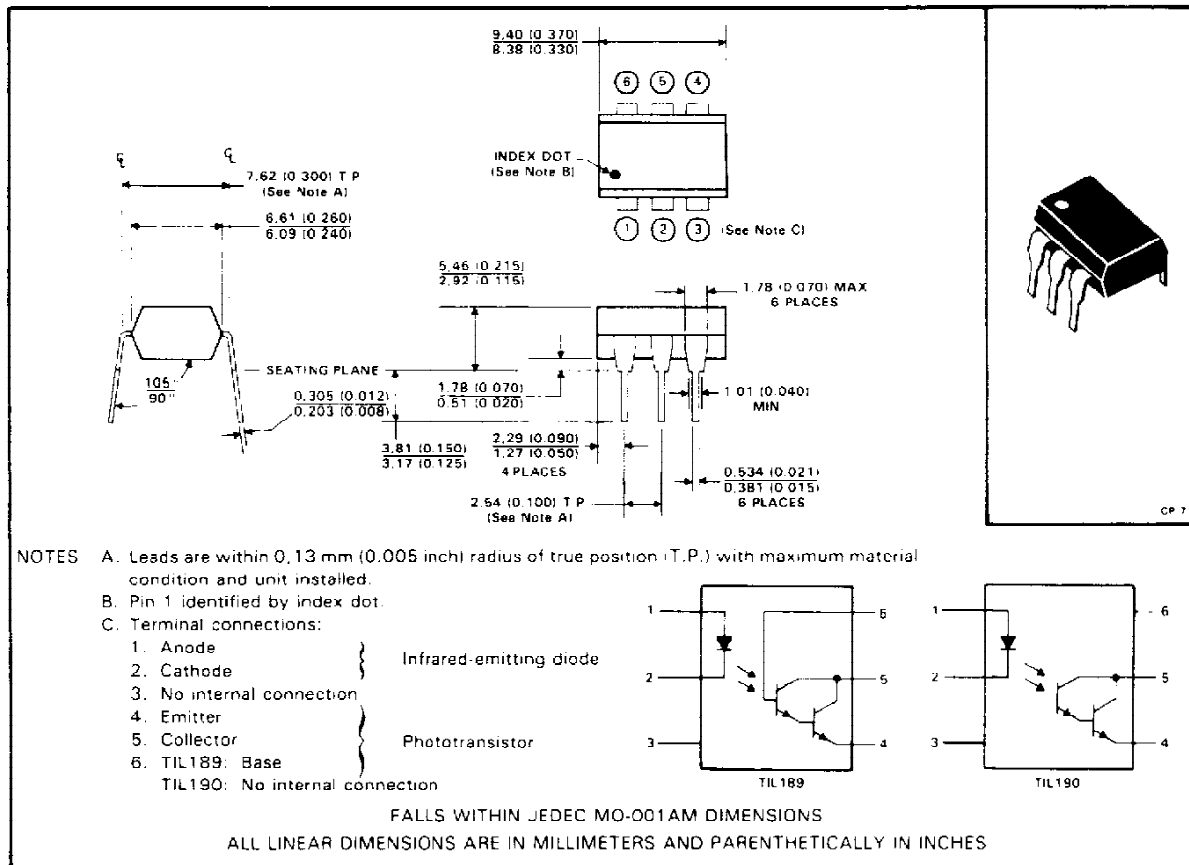
SOOS038A D2987, JANUARY 1987—REVISED JULY 1989

- High Direct-Current Transfer Ratios, 500% Minimum at $I_f = 10$ mA and Up to 1500% at $I_f = 2$ mA with Choice of Four Categories
- Plastic Dual-In-Line Package
- High-Voltage Electrical Isolation, 3.535 kV Peak (2.5 kV rms)
- Gallium Arsenide Diode Infrared Source Optically Coupled to a Silicon N-P-N Darlington Phototransistor
- No Base Lead Connection on TIL190 for High-EMI Environment
- UL Recognized — File # E65085

description

The TIL189 and TIL190 Optocouplers are designed for use in applications that require high current transfer ratio and high voltage isolation between the input and output. The TIL189 has the base connected for applications where a base signal or resistor is required. The TIL190 is designed with no internal base connection for applications where high base-noise immunity is desired. Users can select from four different current gains (TIL189-1 through TIL189-4 and TIL190-1 through TIL190-4).

mechanical data



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absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Input-to-output voltage	±3.535 kV peak or dc (±2.5 kV rms)
Collector-base voltage (TIL189)	100 V
Collector-emitter voltage (see Note 1)	55 V
Emitter-collector voltage	7 V
Emitter-base voltage (TIL189)	14 V
Input diode reverse voltage	3 V
Input diode continuous forward current at (or below)	
25°C free-air temperature (see Note 2)	100 mA
Continuous power dissipation at (or below) 25°C free-air temperature:	
Infrared-emitting diode (see Note 3)	150 mW
Phototransistor (see Note 3)	150 mW
Total, infrared-emitting diode plus phototransistor (see Note 4)	250 mW
Storage temperature range	-55°C to 150°C
Lead temperature 1,6 mm (1/16-inch) from case for 10 seconds	260°C

- NOTES: 1. This value applies when the base-emitter diode is open circuited.
2. Derate linearly to 100°C free-air temperature at the rate of 1.33 mA/°C.
3. Derate linearly to 100°C free-air temperature at the rate of 2 mW/°C.
4. Derate linearly to 100°C free-air temperature at the rate of 3.33 mW/°C.

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electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TIL189			TIL190			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = 10 \mu A, I_E = 0, I_F = 0$	100						V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = 1 mA, I_B = 0, I_F = 0$	55			65			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = 10 \mu A, I_C = 0, I_F = 0$	14						V
$V_{(BR)ECO}$	Emitter-collector breakdown voltage	$I_E = 100 \mu A, I_F = 0$				7			V
I_R	Input diode static reverse current	$V_R = 3 V$				10			μA
$I_{C(on)}$	On-state collector current	Photo-transistor operation $V_{CE} = 1 V, I_F = 2 mA, I_B = 0$	TIL189-1, TIL190-1			5			mA
			TIL189-2, TIL190-2			10			
			TIL189-3, TIL190-3			20			
			TIL189-4, TIL190-4			30			
		$V_{CE} = 1 V, I_F = 10 mA, I_B = 0$	50			50			
	Photodiode operation	$V_{CB} = 1 V, I_F = 10 mA, I_E = 0$	5	15				μA	
$I_{C(off)}$	Off-state collector current	$V_{CE} = 10 V, I_F = 0, I_B = 0$	1			100			nA
h_{FE}	Transistor static forward current transfer ratio	$V_{CE} = 1 V, I_C = 10 mA, I_F = 0$	25000						
V_F	Input diode static forward voltage	$I_F = 10 mA$	1.2			1.5			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = 50 mA, I_F = 10 mA, I_B = 0$	0.87			1			V
r_{iD}	Input-to-output internal resistance	$V_{in-out} = \pm 500 V, \text{ See Note 5}$	10^{11}			10^{11}			Ω
C_{io}	Input-to-output capacitance	$V_{in-out} = 0, f = 1 MHz, \text{ See Note 5}$	1			1.3			pF

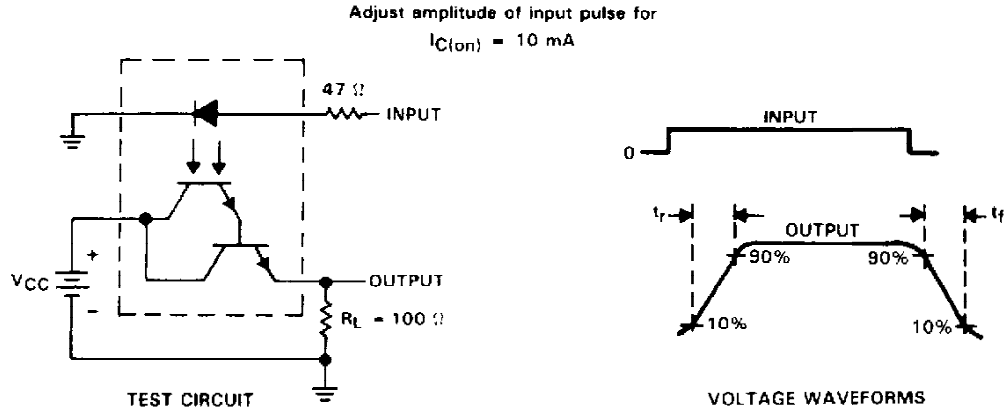
NOTE 5: These parameters are measured between both input-diode leads shorted together and all the phototransistor leads shorted together.

switching characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS	TIL189			TIL190			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
t_r Rise time	$V_{CC} = 10 V, I_{C(on)} = 10 mA,$	100			100			μs
t_f Fall time	$R_L = 100 \Omega, \text{ see Figure 1}$	100			100			μs

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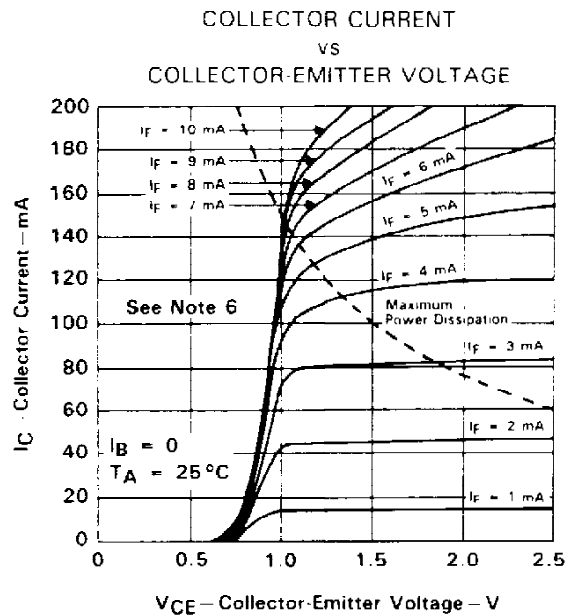
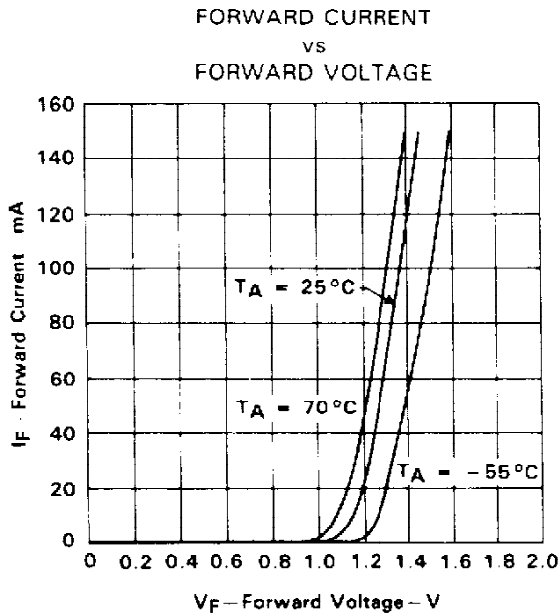
PARAMETER MEASUREMENT INFORMATION



NOTES: A The input waveform is supplied by a generator with the following characteristics: $Z_0 = 50 \Omega$, $t_r \leq 15 \text{ ns}$, duty cycle = 1%.
B The output waveform is monitored on an oscilloscope with the following characteristics: $t_f \leq 12 \text{ ns}$, $R_1 \geq 1 \text{ M}\Omega$, $C_{IN} \leq 20 \text{ pF}$.

FIGURE 1. SWITCHING TIMES

TYPICAL CHARACTERISTICS



NOTE 6 Pulse operation is required for operation beyond limits shown by the dashed line.

TYPICAL CHARACTERISTICS

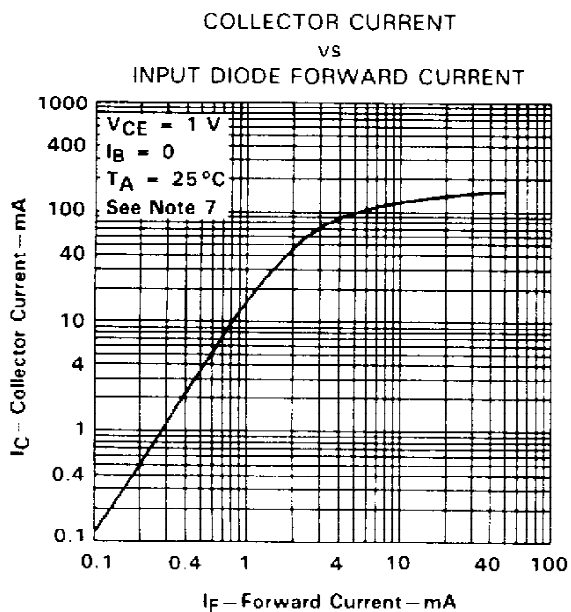


FIGURE 4

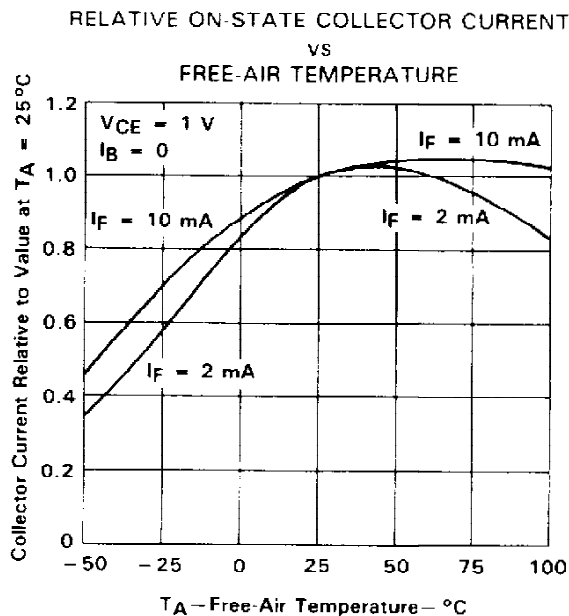


FIGURE 5

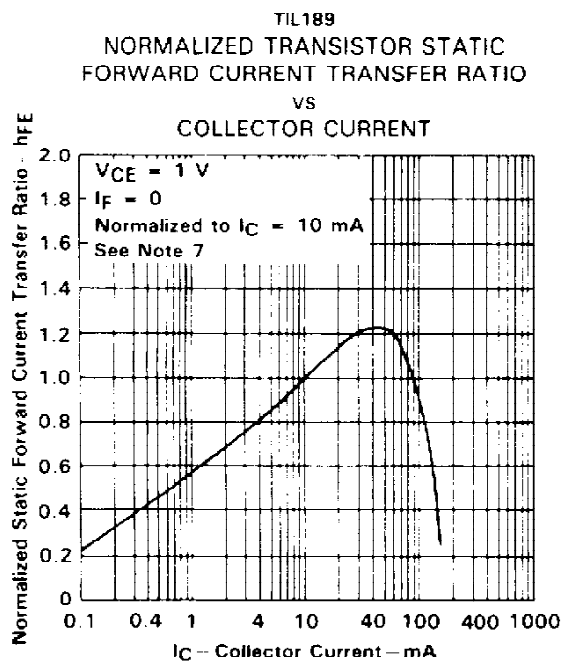


FIGURE 6

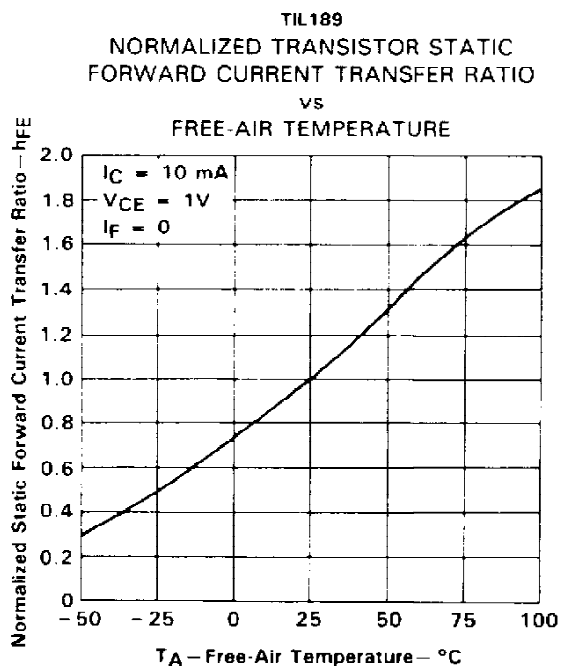


FIGURE 7

NOTE 7: These parameters were measured using pulse techniques $t_w = 1$ ms, duty cycle $\leq 2\%$.

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TYPICAL CHARACTERISTICS

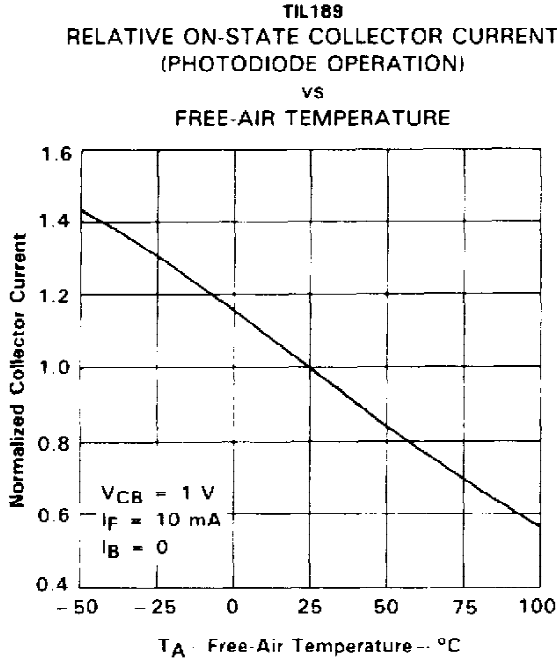


FIGURE 8

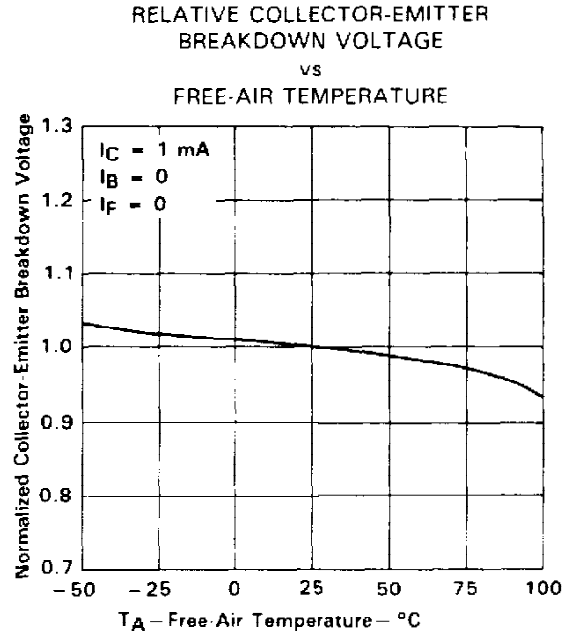


FIGURE 9

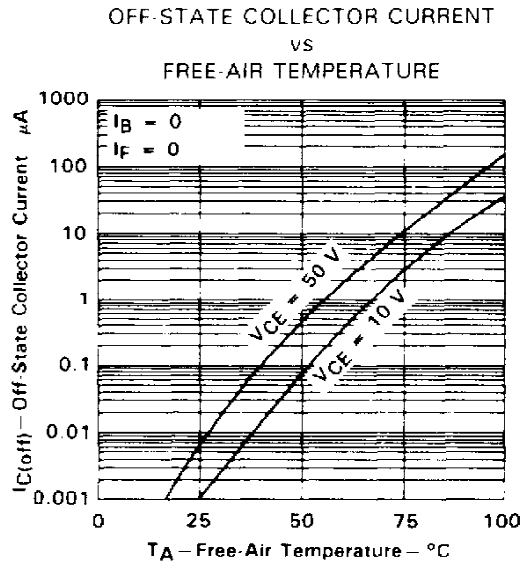


FIGURE 10

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